

Stable PbI₂-Terminated (001) Facets Drive Low-Defect Anisotropy for High-Performance Charge Transport in MAPbI₃ Single Crystals

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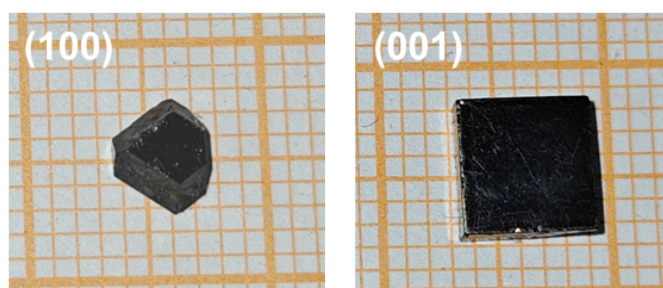


Fig. S1. Optical images of (100)- and (001)-oriented MAPbI₃ bulk single crystals.

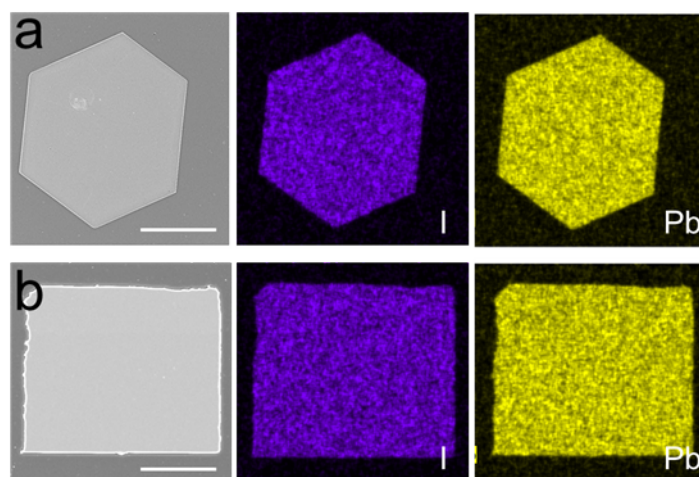


Fig. S2. SEM and EDS mapping of (a) MAPbI₃-(100) and (b) MAPbI₃-(001) facets. Scale bars are 20 μ m.

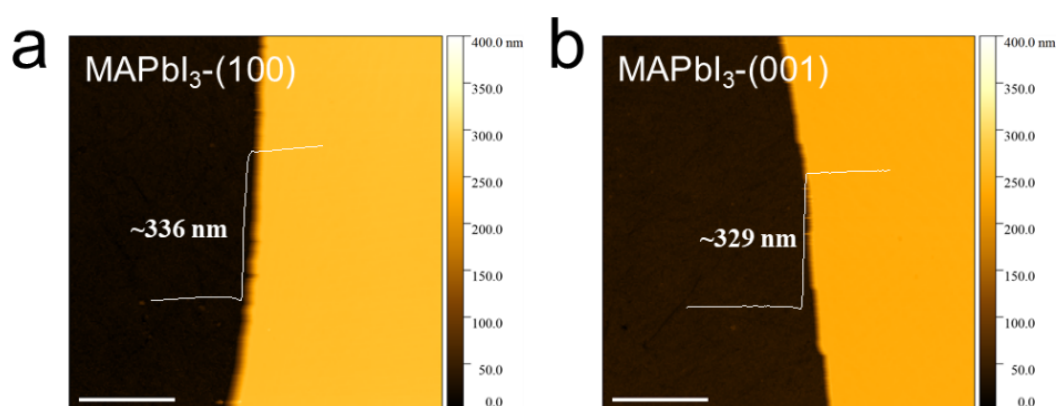


Fig. S3. AFM thickness measurements of the (a) MAPbI₃-(100) and (b) MAPbI₃-(001) facets.

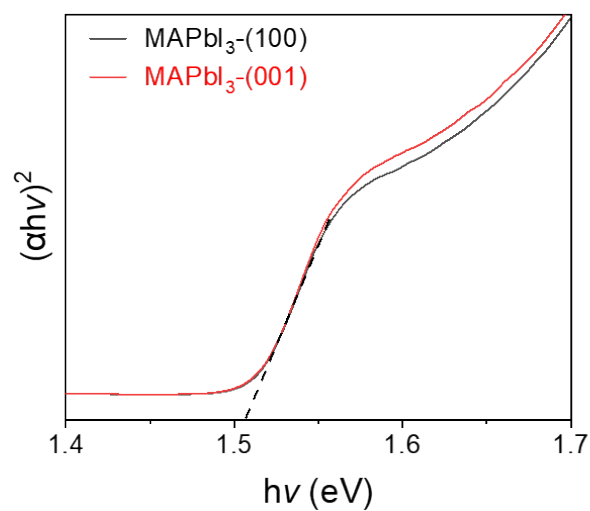


Fig. S4. Tauc plots of (100) and (001) facets of MAPbI₃ single crystals.

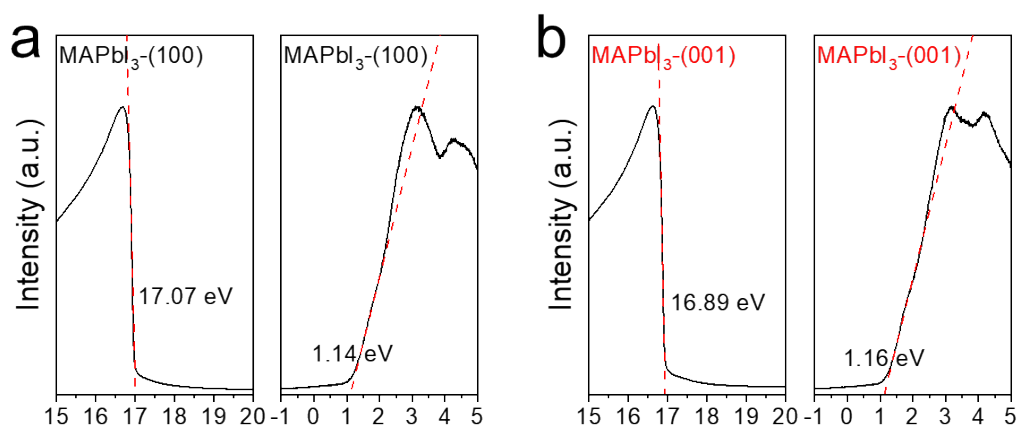


Fig. S5. UPS spectra of (a) MAPbI₃-(100) and (b) MAPbI₃-(001) facets.

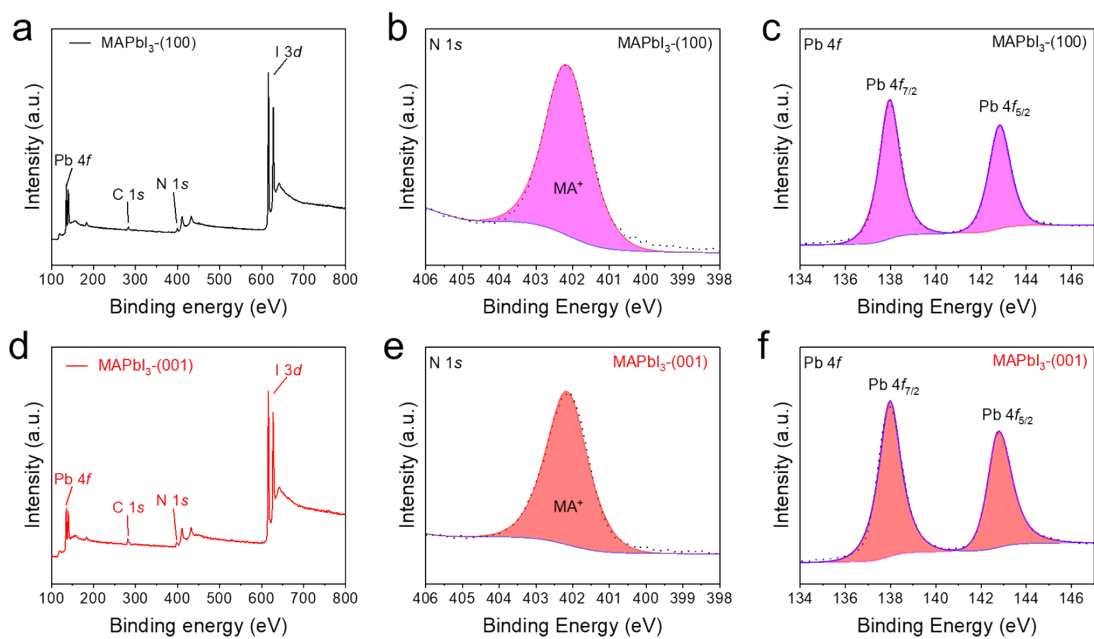


Fig. S6. (a–c) show the XPS survey scan, N 1s, and Pb 4f core-level spectra of the MAPbI₃-(100) facet, respectively. The corresponding spectra from the MAPbI₃-(001) facet are displayed in (d–f).

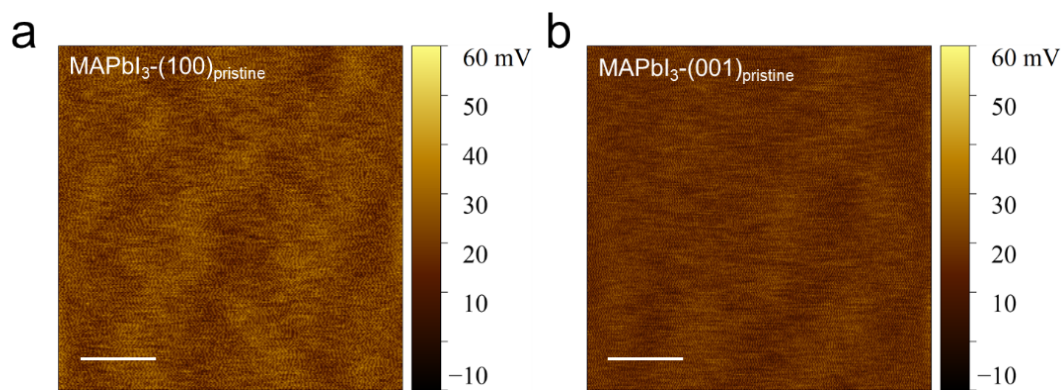


Fig. S7. Surface-potential images of the pristine (a) MAPbI₃-(100) and (b) MAPbI₃-(001) facets, respectively. The scale bar is 5 μ m.

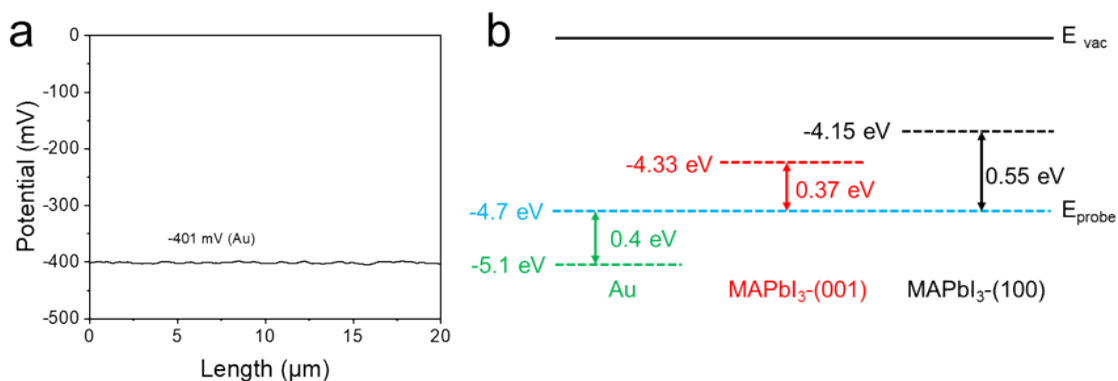


Fig. S8. Work function calibration of the KPFM probe. (a) Surface potential map of the 100 nm Au reference film on Si wafer. (b) Relative Fermi level alignment with respect to the vacuum level.

Prior to measurements, the probe work function was calibrated against a freshly evaporated Au reference (5.1 eV). The observed contact potential difference (CPD) of -401 mV yielded a calibrated probe work function of -4.7 eV. Post-calibration, CPD values of +550 mV (100) and +370 mV (001) were measured, corresponding to work functions of -4.15 eV and -4.33 eV, respectively.

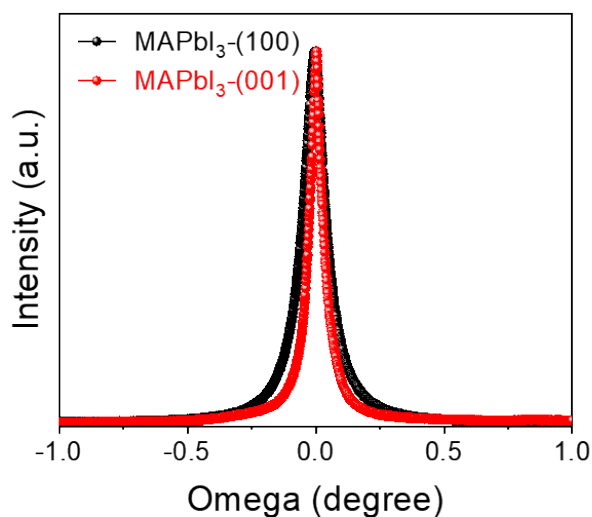


Fig. S9. XRD rocking curves of MAPbI₃-(100) and MAPbI₃-(001) facets.

Table S1. The full width at half-maximum (FWHM) of XRD rocking curves of MAPbI₃-(100) and MAPbI₃-(001) facets

Samples	FWHM of rocking curve (°)
MAPbI ₃ -(100)	0.158
MAPbI ₃ -(001)	0.103

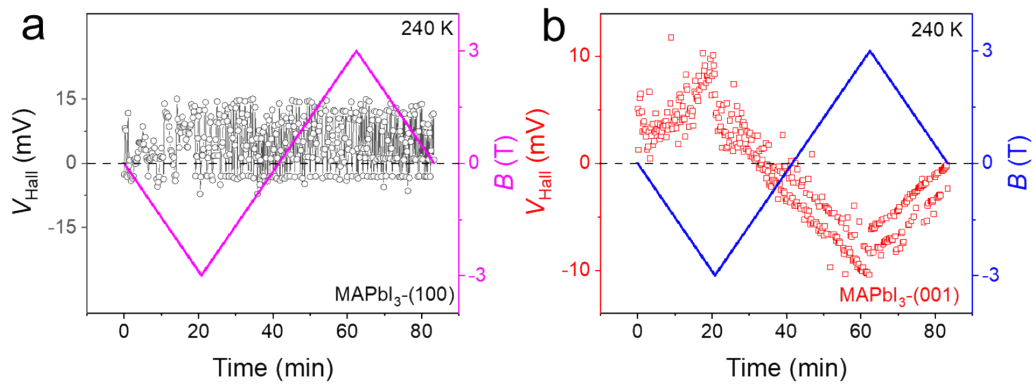


Fig. S10. Hall voltage measurements of (a) MAPbI₃-(100) and (b) MAPbI₃-(001) facets at 240 K. Hall measurements for the (100) facet at 240 K were precluded, presumably by ion migration.

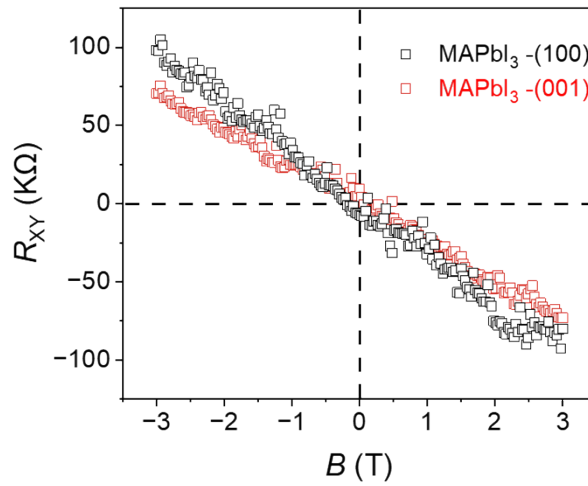


Fig. S11. Corresponding Hall resistance R_{xy} profile (180K) with respect to an external magnetic field B .

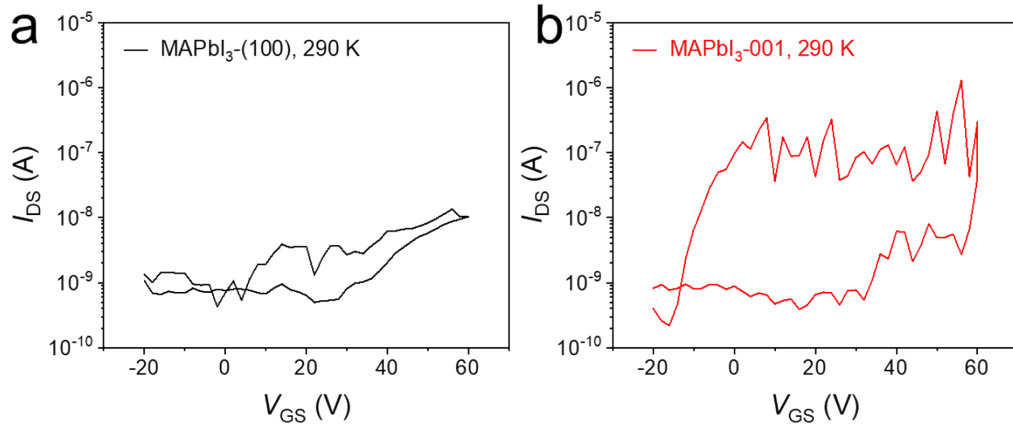


Fig. S12. Transfer characteristics of (a) MAPbI₃-(100) and (b) MAPbI₃-(001) facets measured at 290 K.

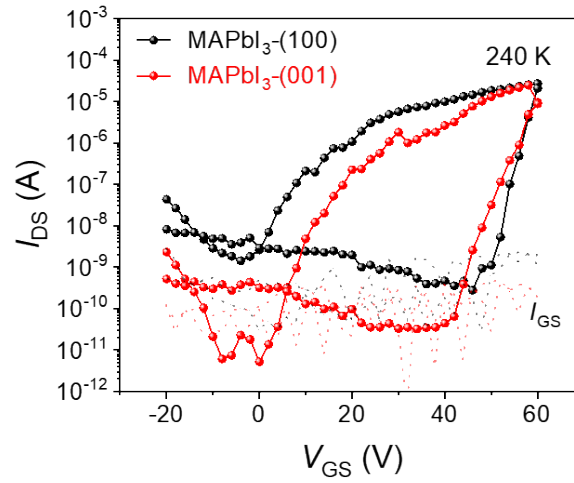


Fig. S13. Transfer characteristics of MAPbI₃-(100) and -(001) facets measured at 240 K.

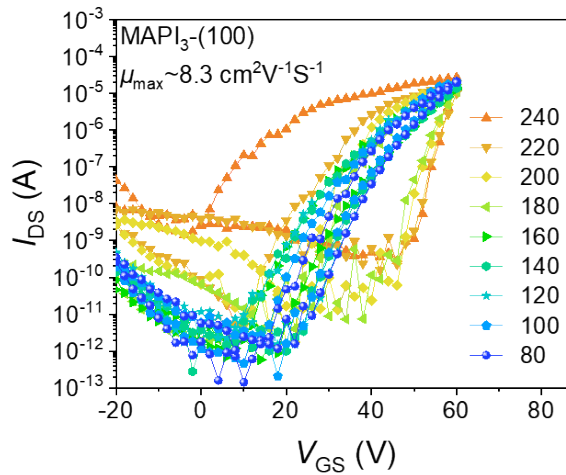


Fig. S14. Temperature dependent transfer curves of MAPbI₃-(100) facet.

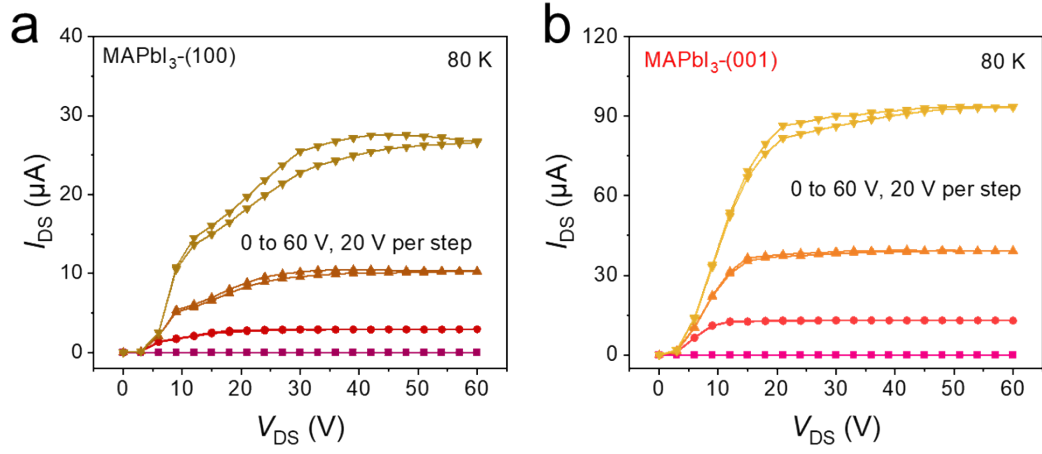


Fig. S15. Out characteristics of (a) MAPbI₃-(100) and (b) MAPbI₃-(001) facets measured at 80 K.

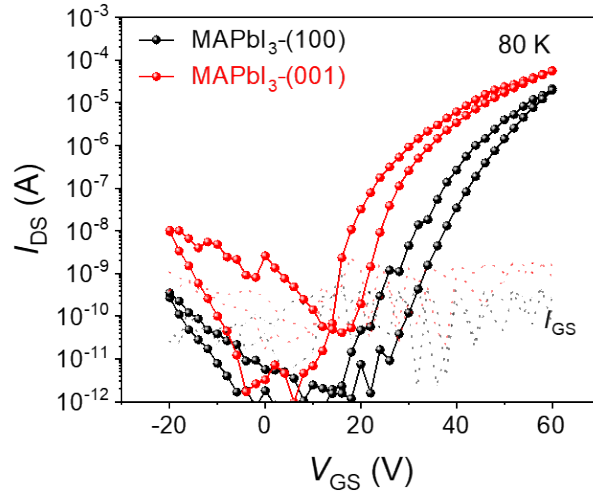


Fig. S16. Transfer characteristics of MAPbI₃-(100) and -(001) facets measured at 80 K.